

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI HF75-50F is Designed for

FEATURES:

- $P_G = 14$ dB min. at 75 W/30 MHz
- $IMD_3 = 50$ dBc max. at 75 W(PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	3.25 A
V_{CB0}	110 V
V_{CE0}	55 V
V_{EBO}	4.0 V
P_{DISS}	127 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
q_{JC}	2.0 $^\circ C/W$

PACKAGE STYLE .380 4L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

ORDER CODE: ASI10610

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 100$ mA	110			V
BV_{CE0}	$I_C = 200$ mA	55			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
h_{FE}	$V_{CE} = 6.0$ V $I_C = 1.4$ A	19	---	50	---
C_{ob}	$V_{CB} = 50$ V $f = 1.0$ MHz			100	pF
G_P		14	---		dB
IMD_3	$V_{CE} = 50$ V $P_{OUT} = 75$ W(PEP)	---	---	-30	dBc
h_c		37			%